Cheng Tai Kuo

List of Publications by Year
in descending order

32	814	623734	477307
papers	citations	14 h-index	29 g-index

32	32	32	1547
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Emergent phenomena at oxide interfaces studied with standing-wave photoelectron spectroscopy. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2022, 40, 020801.	2.1	2
2	Probing the polar-nonpolar oxide interfaces using resonant x-ray standing wave techniques. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2022, 40, 010804.	2.1	1
3	Orientation-Controlled Anisotropy in Single Crystals of Quasi-1D BaTiS₃. Chemistry of Materials, 2022, 34, 5680-5689.	6.7	6
4	Interface Carriers and Enhanced Electronâ€Phonon Coupling Effect in Al₂O₃/TiO₂ Heterostructure Revealed by Resonant Inelastic Soft Xâ€Ray Scattering. Advanced Functional Materials, 2021, 31, 2104430.	14.9	5
5	High resolution depth profiling using near-total-reflection hard x-ray photoelectron spectroscopy. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2021, 39, .	2.1	5
6	Orbital contributions in the element-resolved valence electronic structure of <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:msub><mml:mi>Bi</mml:mi><mml:mn>2</mml:mn></mml:msub></mml:mrow></mml:math> Physical Review B, 2021, 104, .	3.2	3
7	Two-dimensional electron systems in perovskite oxide heterostructures: Role of the polarity-induced substitutional defects. Physical Review Materials, 2020, 4, .	2.4	7
8	Hard x-ray standing-wave photoemission insights into the structure of an epitaxial Fe/MgO multilayer magnetic tunnel junction. Journal of Applied Physics, 2019, 126, 075305.	2.5	9
9	Depth-resolved resonant inelastic x-ray scattering at a superconductor/half-metallic-ferromagnet interface through standing wave excitation. Physical Review B, 2018, 98, .	3.2	6
10	Interface properties and built-in potential profile of a <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mrow><mml:mspace width="4pt" /><mml:mi>LaCr</mml:mi></mml:mrow><mml:msub><mml:mi mathvariant="normal">O</mml:mi><mml:mn>3</mml:mn></mml:msub><mml:mo>/</mml:mo><mml:mi>SrTi</mml:mi><mml:msub><mml:mi mathvariant="normal">O</mml:mi><mml:mn>3</mml:mn></mml:msub></mml:mrow></mml:math> superlattice. Physical Review B, 2018,	3.2	22
11	Element- and momentum-resolved electronic structure of the dilute magnetic semiconductor manganese doped gallium arsenide. Nature Communications, 2018, 9, 3306.	12.8	22
12	Characterization of free-standing InAs quantum membranes by standing wave hard x-ray photoemission spectroscopy. APL Materials, 2018, 6, .	5.1	11
13	Element- and momentum-resolved electronic structure of the dilute magnetic semiconductor manganese doped gallium arsenide. Nature Communications, 2018, 9, 3306.	12.8	22
14	Nitride Semiconductor Nanorod Heterostructures for Full-Color and White-Light Applications. Semiconductors and Semimetals, 2017, 96, 341-384.	0.7	3
15	X-ray Absorption Spectroscopy Study of the Effect of Rh doping in Sr2IrO4. Scientific Reports, 2016, 6, 23856.	3.3	15
16	Exfoliation and Raman Spectroscopic Fingerprint of Few-Layer NiPS3 Van der Waals Crystals. Scientific Reports, 2016, 6, 20904.	3.3	222
17	Superconductor to Mott insulator transition in YBa2Cu3O7/LaCaMnO3 heterostructures. Scientific Reports, 2016, 6, 33184.	3.3	10
18	The energy band alignment at the interface between mechanically exfoliated few-layer NiPS3 nanosheets and ZnO. Current Applied Physics, 2016, 16, 404-408.	2.4	14

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19	Insulating-layer formation of metallic LaNiO3 on Nb-doped SrTiO3 substrate. Applied Physics Letters, 2015, 106, 121601.	3.3	10
20	Experimental Determination of Electron Affinities for InN and GaN Polar Surfaces. Applied Physics Express, 2012, 5, 031003.	2.4	35
21	Natural band alignments of InN/GaN/AlN nanorod heterojunctions. Applied Physics Letters, 2011, 99, 122101.	3.3	14
22	Plasmonic Green Nanolaser Based on a Metalâ€“Oxideâ€“Semiconductor Structure. Nano Letters, 2011, 11, 4256-4260.	9.1	106
23	Spontaneous-polarization-induced heterojunction asymmetry in III-nitride semiconductors. Applied Physics Letters, 2011, 99, 022113.	3.3	6
24	Is electron accumulation universal at InN polar surfaces?. Applied Physics Letters, 2011, 98, .	3.3	46
25	Effects of (NH4)2Sx treatment on indium nitride surfaces. Journal of Applied Physics, 2010, 107, 043710.	2.5	18
26	Direct imaging of GaN p-n junction by cross-sectional scanning photoelectron microscopy and spectroscopy. Applied Physics Letters, 2009, 94, .	3.3	9
27	Valence band offset and interface stoichiometry at epitaxial Si3N4/Si(111) heterojunctions formed by plasma nitridation. Applied Physics Letters, 2009, 95, .	3.3	22
28	Electronic Properties of III-Nitride Surfaces and Interfaces Studied by Scanning Photoelectron Microscopy and Spectroscopy. Materials Research Society Symposia Proceedings, 2009, 1202, 38.	0.1	0
29	Absence of Fermi-Level Pinning at Cleaved Nonpolar InN Surfaces. Physical Review Letters, 2008, 101, 106803.	7.8	87
30	Cross-sectional scanning photoelectron microscopy and spectroscopy of wurtzite InNâˆ•GaN heterojunction: Measurement of â€œintrinsicâ€•band lineup. Applied Physics Letters, 2008, 92, .	3.3	39
31	Immobilization of DNA-Au nanoparticles on aminosilane-functionalized aluminum nitride epitaxial films for surface acoustic wave sensing. Applied Physics Letters, 2008, 93, .	3.3	19
32	Polarization-induced valence-band alignments at cation- and anion-polar InNâˆ•GaN heterojunctions. Applied Physics Letters, 2007, 91, .	3.3	35